

FORM PTO-1449

Docket Number (Optional)

81784.0182

Application Number

09/148,606

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

Applicant

Kiyoshi YONEDA et al.

Filing Date

September 4, 1998

Group Art Unit

2774

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER							DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
AZ	4	4	6	6	1	7	9	8/84	Kasten	29	576	10/19/82
AZ	5	1	4	5	8	0	8	9/92	Sameshima et al.	437	174	8/1/94
AZ	5	5	2	9	9	5	1	6/96	Noguchi et al.	437	RE74	11/1/94
AZ	5	9	6	0	3	2	3	9/99	Wakita et al.	438	795	10/17/97

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Technology Center 2600

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER							DATE	COUNTRY	CLASS	SUBCLASS	Translation	
												YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

AZ	Kubo et al., "Characteristics of Polycrystalline-Si Thin Film Transistors Fabricated by Excimer Laser Annealing Method", IEEE Transactions on Electron Devices, Oct. 1994, pp. 1876-1879
AZ	Kohno et al., "High Performance Poly-Si TFTs Fabricated Using Pulsed Laser Annealing and Remote Plasma CVD With Low Temperature Processing", IEEE Transactions on Electron Devices, Feb. 1995, pp. 251-257
AZ	Kuriyama, "Excimer Laser Crystallization of Silicon Films for AMLCDs", AMLCK Second International Workshop on Active Matrix Liquid Crystal Displays, Sept. 1995, pp. 87-92

EXAMINER

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DATE CONSIDERED

08-09-01

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.